

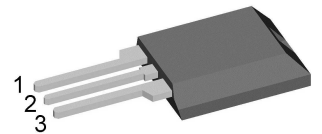
# HiPerFRED

$V_{RRM} = 2 \times 600 \text{ V}$   
 $I_{FAV} = 15 \text{ A}$   
 $t_{rr} = 25 \text{ ns}$

High Performance Fast Recovery Diode  
 Low Loss and Soft Recovery  
 Phase leg

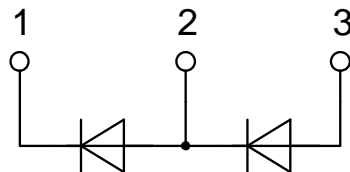
Part number

**DSEE15-12CC**



Backside: isolated

E72873



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

### Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

### Package: ISOPLUS220

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

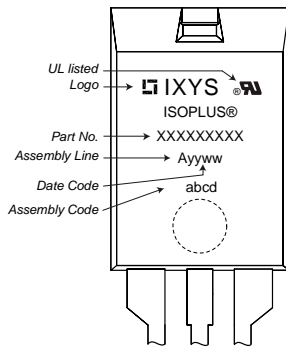
- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

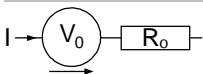
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V	
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V	
$I_R$	reverse current, drain current	$V_R = 600 V$	$T_{VJ} = 25^{\circ}C$		100	$\mu A$	
		$V_R = 600 V$	$T_{VJ} = 150^{\circ}C$		0.5	mA	
$V_F$	forward voltage drop	$I_F = 15 A$	$T_{VJ} = 25^{\circ}C$		2.04	V	
		$I_F = 30 A$			2.25	V	
		$I_F = 15 A$	$T_{VJ} = 150^{\circ}C$		1.35	V	
		$I_F = 30 A$			1.59	V	
$I_{FAV}$	average forward current	$T_C = 140^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}C$		15	A	
$V_{FO}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}C$		0.99	V	
$r_F$	slope resistance				15	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				1.6	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.50		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		95	W	
$I_{FSM}$	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		110	A	
$C_J$	junction capacitance	$V_R = 400 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		12	pF	
$I_{RM}$	max. reverse recovery current	} $I_F = 15 A; V_R = 300 V$ $-di_F / dt = 600 A/\mu s$	$T_{VJ} = 25^{\circ}C$		11	A	
			$T_{VJ} = 100^{\circ}C$		19	A	
$t_{rr}$	reverse recovery time		$T_{VJ} = 25^{\circ}C$		25	ns	
			$T_{VJ} = 100^{\circ}C$		83	ns	

Package ISOPLUS220		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			35	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				2		g
$F_C$	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	1.0			mm
$d_{Spb/Apb}$		terminal to backside	3.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V

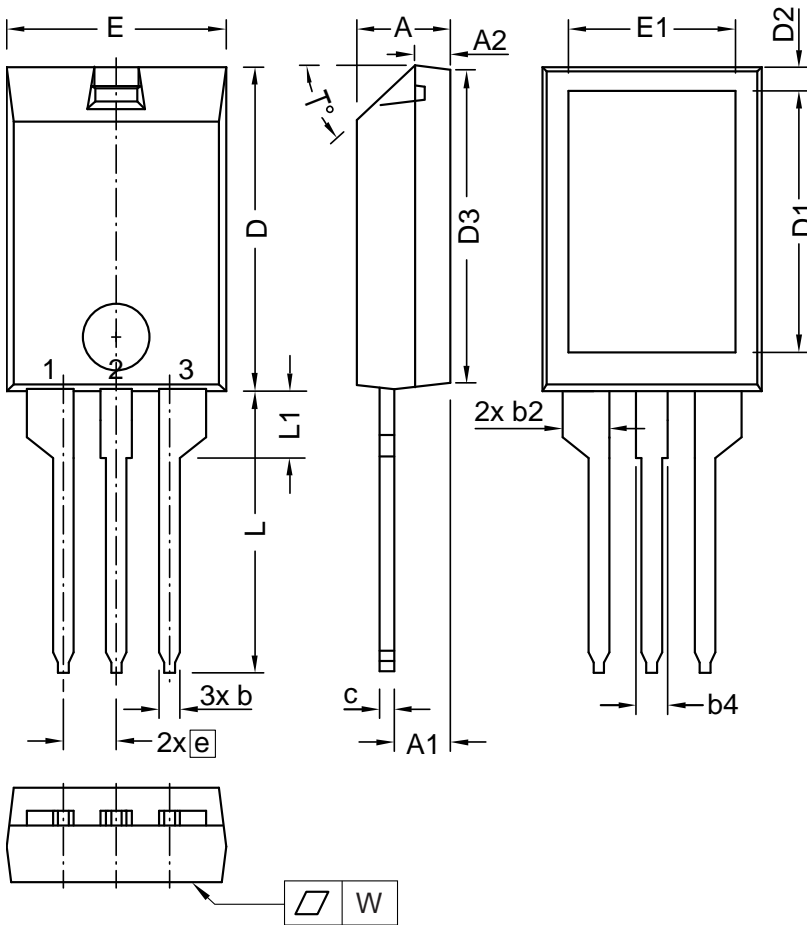
**Product Marking**


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEE15-12CC	DSEE15-12CC	Tube	50	500725

**Equivalent Circuits for Simulation**
*\* on die level*
 $T_{VJ} = 175\text{ °C}$ 

**Fast Diode**

$V_{0\ max}$	threshold voltage	0.99	V
$R_{0\ max}$	slope resistance *	11.3	mΩ

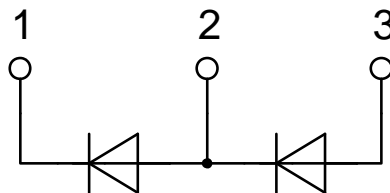
## Outlines ISOPLUS220



Dim.	Millimeters		Inches	
	min	max	min	max
A	4.00	5.00	0.157	0.197
A1	2.50	3.00	0.098	0.118
A2	1.60	1.80	0.063	0.071
b	0.90	1.30	0.035	0.051
b2	2.35	2.55	0.093	0.100
b4	1.25	1.65	0.049	0.065
c	0.70	1.00	0.028	0.039
D	15.00	16.00	0.591	0.630
D1	12.00	13.00	0.472	0.512
D2	1.10	1.50	0.043	0.059
D3	14.90	15.50	0.587	0.610
E	10.00	11.00	0.394	0.433
E1	7.50	8.50	0.295	0.335
e	2.54 BSC		0.100 BSC	
L	13.00	14.50	0.512	0.571
L1	3.00	3.50	0.118	0.138
T°	42.5	47.5		
W	-	0.1	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite  
*The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side*

Die Gehäuseabmessungen entsprechen dem Typ TO-273 gemäß JEDEC außer D und D1.  
*This drawing will meet all dimensions requirement of JEDEC outline TO-273 except D and D1.*



**Fast Diode**

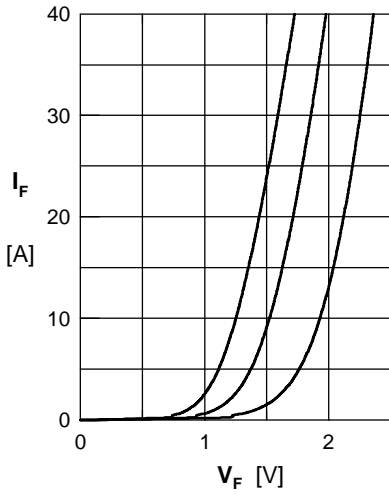


Fig. 1 Forward current  $I_F$  vs.  $V_F$

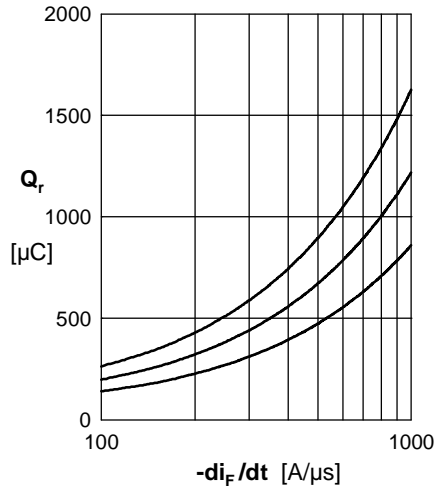


Fig. 2 Typ. reverse recovery charge  $Q_{rr}$  versus  $-di_F/dt$

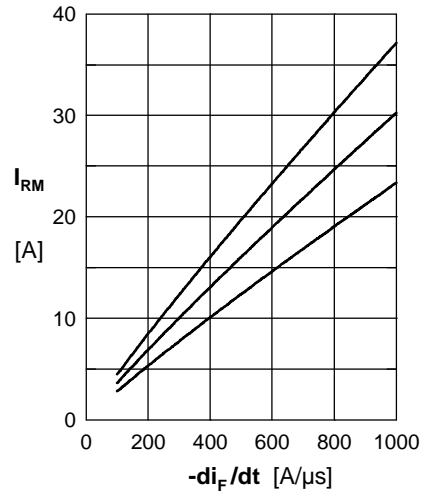


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$

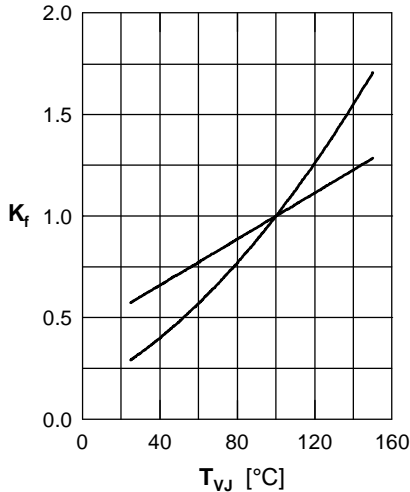


Fig. 4 Dynamic parameters  $K_f$ ,  $I_{RM}$  versus  $T_{VJ}$

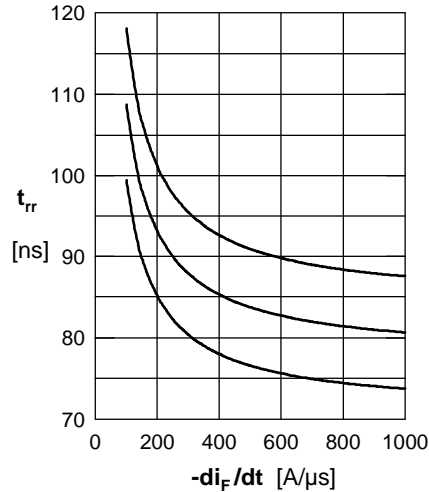


Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$

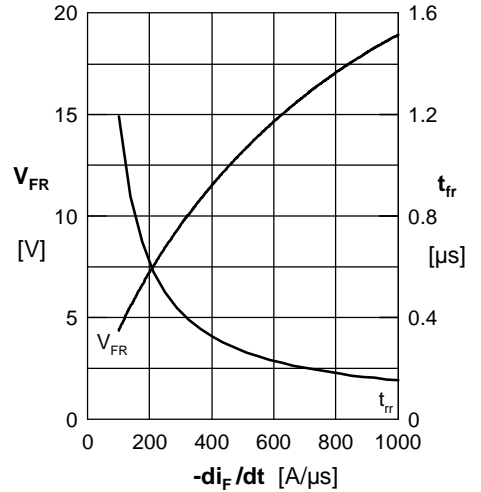


Fig. 6 Typ. peak forward voltage  $V_{FR}$  and typ. forward recovery time  $t_{fr}$  versus  $di_F/dt$

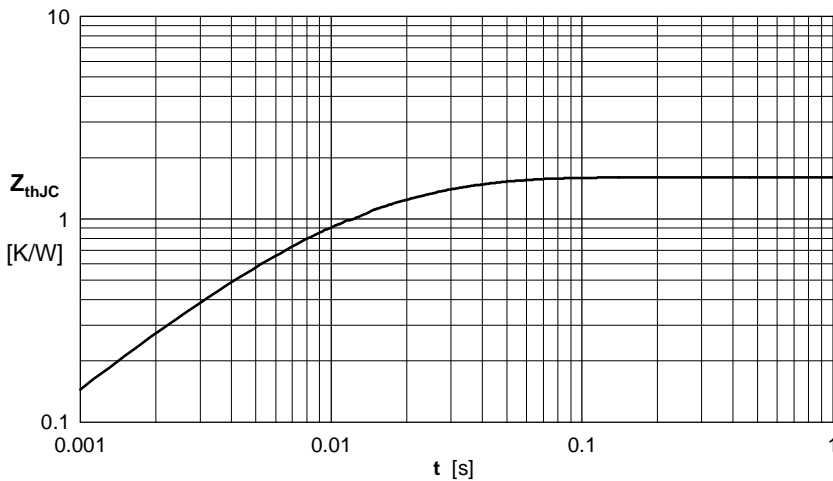


Fig. 7 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.908	0.0052
2	0.350	0.0003
3	0.342	0.017